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thin solid films

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Contents

Preface
M.A. Herman 1

Growth Physics and Low Dimensional Structures

Fundamental growth processes in the molecular beam epitaxy of III–V compounds – an historical perspective
B.A. Joyce 3

Selective area MBE of GaAs, A1As and their alloys by periodic supply epitaxy
T. Nishinaga, G. Bacchin 6

Molecular layer epitaxy
J.-I. Nishizawa, T. Kurabayashi 13

Laser-focused atomic deposition – nanofabrication via atom optics
J.J. McClelland, R.J. Celotta 25

A simple solid-on-solid model of epitaxial thin films growth: inhomogeneous multilayered sandwiches
K. Malarz, A.Z. Maksymowicz 28

Uniform III–V semiconductor quantum wire and quantum dot arrays by natural self-faceting on patterned substrates
K.H. Ploog, R. Nötzel 32

Quantum dots formed by ultrathin insertions in wide-gap matrices
N.N. Ledentsov, I.L. Krestnikov, M. Straßburg, R. Engelhardt, S. Rodt, R. Heitz, U.W. Pohl, A. Hoffmann, D. Bimberg, A.V. Sakharov, W.V. Lundin, A.S. Usikov, Zh.I. Alferov, D. Litvinov, A. Rosenauer, D. Gerthsen 40

Equilibrium shape of steps and islands on polar CdTe(001) surface: application to the preparation of self organized templates for growth of nanostructures
D. Martrou, N. Magnea 48

MBE growth and applications of silicon interface control layers
H. Hasegawa 58

Formation and properties of self-organized II–VI quantum islands
E. Kurtz, J. Shen, M. Schmidt, M. Grün, S.K. Hong, D. Litvinov, D. Gerthsen, T. Oka, T. Yao, C. Klingshirn 68

Molecular beam epitaxy of silicon–germanium nanostructures
O.P. Pchelyakov, Y.B. Bolkhovityanov, A.V. Dvurechenskii, A.I. Nikiforov, A.I. Yakimov, B. Voigtländer 75

InAs quantum dots embedded in silicon
L. Hansen, F. Bensing, A. Waag. 85

Growth and electrical characteristics of InAs/GaAs quantum well and quantum dot structures
Z.J. Horváth, L. Dózsa, V. Van Tuyen, B. Pődör, Á. Nemcsics, P. Frigeri, E. Gombia, R. Mosca, S. Franchi 89

Single-electron charging of self assembled quantum dots
B. Szafran, J. Adamowski, S. Bednarek 93

MBE-grown gate-controlled quantum-dot nanostructure and its current–voltage characteristics
S. Bednarek, B. Szafran, J. Adamowski 97

Materials – Related Growth Processes and Characterization

MBE growth and properties of supersaturated, carbon-containing silicon/germanium alloys on Si(001)
H.J. Osten 101

MBE-growth peculiarities of fluoride (CdF_2–CaF_2) thin film structures
N.S. Sokolov, S.M. Suturin 112

Strain-relaxed SiGe/Si heteroepitaxial structures of low threading-dislocation density
P.I. Gaiduk, A.N. Larsen, J.L. Hansen 120

Auger electron spectroscopy in the investigation of ultrathin films in molecular beam epitaxy
S. Mróz, A. Mróz 126

Structure and electronic properties of ionic nano-layers MBE-grown on III–V semiconductors
M. Szymonski, P. Korecki, J. Kolodziej, P. Czuba, P. Piatkowski 134

UHV-REM study of gold adsorption on the Si(111) surface
A.V. Latyshev, D.A. Nasimov, V.N. Savenko, A.L. Aseev 142

Imaging wurtzite GaN surfaces by molecular beam epitaxy-scanning tunneling microscopy
Q.K. Xue, Q.Z. Xue, S. Kuwano, T. Sakurai, T. Ohno, I.S.T. Tsong, X.G. Qiu, Y. Segawa 149

Investigations on the growth mechanism of wide-gap II–VI semiconductors by means of reflection high energy electron diffraction
J. Griesche 159

Structural propertiles of MBE grown GaMnAs layers
J. Sadowski, J.Z. Domagała, J. Bąk-Misiuk, S. Koleśnik, K. Świątek, J. Kanski, L. Ilver 165

Influence of Mn content in MBE-grown $Sn_{1-x}Mn_xTe$ layers on their structural properties studied by X-ray diffraction
R. Diduszko, V. Domuchowski, A.J. Nadolny, J. Sadowski 168

The elastic strain and composition of self-assembled GeSi islands on Si(001)
Z.F. Krasil'nik, I.V. Dolgov, Y.N. Drozdov, D.O. Filatov, S.A. Gusev, D.N. Lobanov, L.D. Moldavskaya, A.V. Novikov, V.V. Postnikov, N.V. Vostokov 171

Ultra low energy SIMS, XTEM and X-ray diffraction methods for the characterization of a MBE grown short period $(Si_nGe_m)_{16}$ superlattices
O.A. Mironov, D.J.F. Fulgoni, C.P. Parry, G.A. Cooke, M.G. Dowsett, E.H.C. Parker, K.D. Chtcherbatchev, J.M. Bassas, A. Romano-Rodriguez, A. Perez-Rodriguez, J.R. Morante 176

Analysis of photoluminescence efficiency and surface recombination velocity of MBE-grown AlGaAs layers
B. Adamowicz, H. Hasegawa 180

Lateral and depth inhomogeneities in Zn-based heterostructures grown on GaAs by MBE
E.F. Venger, Y.G. Sadof'ev, G.N. Semenova, N.E. Korsunskaya, V.P. Klad'ko, L.V. Shechovtsov, M.P. Semtsiv, L.V. Borkovskaya, S.Y. Sapko 184

Magnetic anisotropy in MBE-grown epitaxial gadolinium ultra-thin films
R. Kalinowski, C. Meyer, A. Wawro, L.T. Baczewski 189

Electronic structure of MBE grown CdYbTe: photoemission studies
K. Szamota-Sadowska, E. Guziewicz, B.J. Kowalski, J. Sadowski, B.A. Orlowski, B. Lesiak-Orlowska, C. Guillot, H. Barrett, R.L. Johnson 193

Manganese fluoride epitaxial growth on Si(111)
O.V. Anisimov, A.G. Banshchikov, A.V. Krupin, M.M. Moisseeva, N.S. Sokolov, V.P. Ulin, N.L. Yakovlev 199

The heteroepitaxy of II–VI compounds on the non-isovalent substrates (ZnTe/Si)
Y.G. Sidorov, M.V. Yakushev, D.N. Pridachin, V.S. Varavin, L.D. Burdina 203

Influence of MBE growth conditions on optical properties of CdTe/ZnTe quantum structures
S. Maćkowski, G. Karczewski, F. Kyrychenko, T. Wojtowicz, J. Kossut 210

Reflectance difference spectroscopy: a powerful tool for in situ investigations of II–VI compounds with Mn
A. Bonanni, K. Hingerl, H. Sitter, D. Stifter 216

Cation diffusion in MBE-grown CdTe layers
A. Seweryn, T. Wojtowicz, G. Karczewski, A. Barcz, R. Jakieła 220

Magneto-optical properties of CdTe quantum wells with ternary MgMnTe and quaternary CdMnMgTe barriers
S. Maćkowski, E. Janik, F. Kyrychenko, J. Kossut 223

Local order of Te impurity atoms and free electron concentration in heavily doped GaAs:Te
T. Slupinski, E. Zielinska-Rohozinska 227

Growth and transport properties of relaxed epilayers of InAs on GaAs
T. Przesławski, A. Wolkenberg, K. Regiński, J. Kaniewski, J. Bąk-Misiuk 232

Interfaces and Device Structures

Quantum dot lasers: breakthrough in optoelectronics
D. Bimberg, M. Grundmann, F. Heinrichsdorff, N.N. Ledentsov, V.M. Ustinov, A.E. Zhukov, A.R. Kovsh, M.V. Maximov, Y.M. Shernyakov, B.V. Volovik, A.F. Tsatsul'nikov, P.S. Kop'ev, Zh.I. Alferov 235

SiGe – heterostructures for CMOS technology
T.E. Whall, E.H.C. Parker 250

Growth of resonant cavity quantum well light emitting diodes and two-junction solar cells by solid source molecular beam epitaxy
M. Pessa, M. Toivonen, P. Savolainen, S. Orsila, P. Sipilä, M. Saarinen, P. Melanen, V. Vilokkinen, P. Uusimaa, J. Haapamaa 260

Transport spectroscopy of quantum wires and superlattices
G. Strasser, G. Ploner, C. Rauch, E. Gornik 267

Transition thickness of semiconductor heteroepitaxy
A. Sasaki, E.R. Weber, Z. Liliental-Weber, S. Ruvimov, J. Washburn, Y. Nabetani 277

GaN substrates for molecular beam epitaxy growth of homoepitaxial structures
I. Grzegory, S. Porowski 281

MBE growth of planar microcavities with distributed Bragg reflectors
K. Regiński, J. Muszalski, M. Bugajski, T. Ochalski, J.M. Kubica, M. Zbroszczyk, J. Kątcki, J. Ratajczak 290

Computer simulations of the transport and electromagnetic properties of MBE-grown quantum structures
K. Kempa, P. Bakshi 295

Pyrometric interferometry during MBE growth of laser heterostructures
J. Muszalski 299

Correlation between the critical layer thickness and the decay time constant of RHEED oscillations in strained $In_xGa_{1-x}As/GaAs$ structures
Á. Nemcsics 302

Author Index of Volume 367 306

Subject Index of Volume 367 308

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